

SEMICONDUCTOR GAS SENSOR AND PROCESS OF ITS MANUFACTURE

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Abstract of RU2143678

FIELD: microelectronics. **SUBSTANCE:** invention refers to technology of manufacture of integrated gas sensors with thin dielectric membranes of 1.0-5.0 μm . Proposed semiconductor gas sensor presents device including dielectric membrane, regions of heater, sensitive layer, electrodes, termination pads and special printed circuit board with working window and lands. Dielectric membrane is arranged above printed circuit board so that regions of heater and sensitive layer are located in opposition to working window and termination pads placed on dielectric membrane are directly coupled to lands of special printed circuit board. Practical realization of invention consists in splitting of plate into crystals at the beginning, in setting of crystal on special printed circuit board with working window arranged opposite to region of heater and in complete pickling of silicon. **EFFECT:** reduced consumption power, prevention of mechanical damage to membrane at stage of splitting of plate into crystals. 2 cl, 1 dwg

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